

RRAM Opportunity for High density memory application

6. Aug. 2014SuOck ChungSK hynix R&D Div.



ICT tech trends

Emerging devices

- . Wearable
- . Automotive
- . Mobile health-care

. IoT

Cloud
Big data
Virtualize
Network

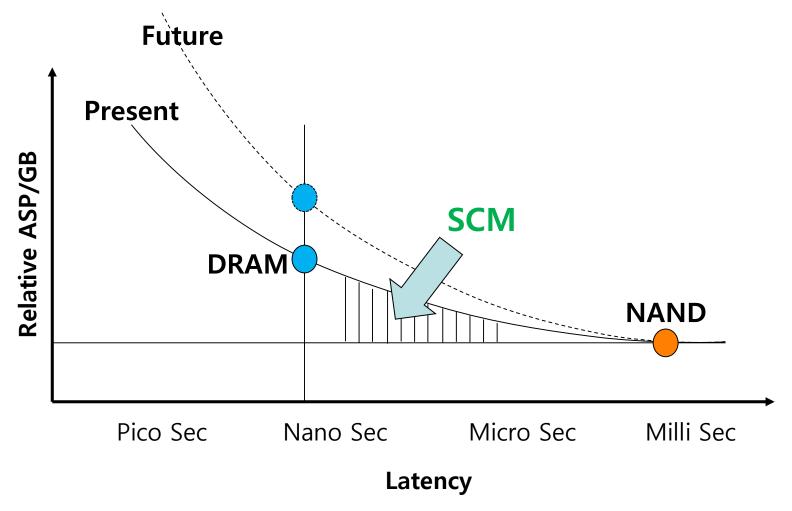


New computing system

- . Exascale
- . Multi-cores
- . New memory technology
 - Byte accessibility
 - Capacity?
 - Latency?
 - Bandwidth / power ?
 - Endurance?
 - → SCM



Flash Memory Gap b/w DRAM ~ NAND





RRAM Potentials

←Low Risk high→	DRAM	NAND	PRAM (SLC)	STTRAM	RRAM (TMO)	RRAM (CBRAM)
Byte-Accessible		•				
Write Latency	•	•	•	•	•	•
Write Bandwidth	•	•		•		
Endurance	•	•		•		
Data Retention	•		•	•	•	
Power / Bandwidth		•	0	•		
3D Solution	•	•		•	•	•
Bit Density (Cost)	0	•	0	•		
Manufacturability	•	•	0	•		0

Requirements for SCM

- Non-volatile, byte accessible
- High capacity + Short latency + Wide B/W @ moderate power

ReRAM is a good candidate

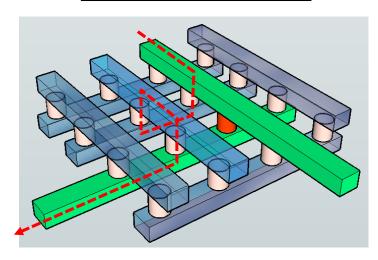
- Smaller power consumption than PRAM (I_reset < 1/3)
- Cross Point Array (XPA) + Multi-Level Stacking (MLS)





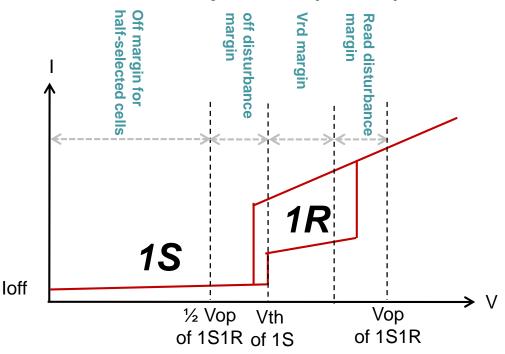
Major challenges

Sneak current effect



- Selected cell → Sneak path
- Originated from imperfect off
- Large operation power,
 Sensing noise issue
- Non-linear 1R → 1S1R Lower the loff of 1S

2 Terminal Operation (1S+1R)



- Simple process merit
- Narrow data window
 - → Good match of 1R+1S I-V
 - → Higher Vop ?



- Recent ICT tech trend requires SCM type memory (high capacity + shorter latency + smaller power). RRAM is an attractive candidate for SCM.
- SK hynix has explored and developed core technologies (especially, cell and array architecture) for RRAM production.
- Stackable selector's I_off and cell data window are key success factors for high density RRAM product.